NSN 5962-01-352-9933

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View Online at https://aerobasegroup.com/nsn/5962-01-352-9933

Body Length:
0.540 inches
Body Width:
Between 0.245 inches and 0.300 inches
Body Height:
Between 0.045 inches and 0.100 inches
Maximum Power Dissipation Rating:
1.1 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and monolithic and electrostatic sensitive
Inclosure Material:
Ceramic
Inclosure Configuration:
Flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
F-9 mil-m-38510
Current Rating Per Characteristic:
190.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
25.00 nanoseconds delay
Memory Device Type:
Pal
Special Features:
Nuclear hardness critical items
Nuclear Hardness Critical Feature:
Hardened
Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type And Quantity:

20 flat leads

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

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